

MOS FIELD EFFECT TRANSISTOR 2SK3740

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3740 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, designed for high voltage applications such as lamp drive, DC/DC converter, and actuator driver.

FEATURES

- Gate voltage rating: ±30 V
- Low on-state resistance

 $R_{DS(on)}$ = 160 m Ω MAX. (V_{GS} = 10 V, I_D = 10 A)

• Low gate charge

 $Q_G = 47 \text{ nC TYP.}$ ($V_{DD} = 200 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 20 \text{ A}$)

• Surface mount package available

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3740-ZK	TO-263 (MP-25ZK)

(TO-263)



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Drain to Source Voltage (V _{GS} = 0 V)	VDSS	250	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±30	V
Drain Current (DC) (Tc = 25°C)	I _{D(DC)}	±20	Α
Drain Current (pulse) Note1	D(pulse)	±60	Α
Total Power Dissipation	P _{T1}	1.5	W
Total Power Dissipation (Tc = 25°C)	P _{T2}	100	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note2	las	20	Α
Single Avalanche Energy Note2	Eas	40	mJ

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 125 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μ H

THERMAL RESISTANCE

Channel to Case Thermal Resistance	Rth(ch-C)	1.25	°C/W	
Channel to Ambient Thermal Resistance	Rth(ch-A)	83.3	°C/W	

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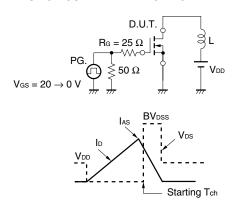


ELECTRICAL CHARACTERISTICS (TA = 25°C)

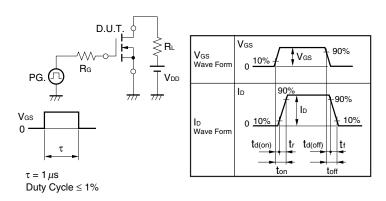
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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 250 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±30 V, V _{DS} = 0 V			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1.0 mA	2.5	3.5	4.5	٧
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 10 A	7.0	15		S
Drain to Source On-state Resistance Note	RDS(on)	V _{GS} = 10 V, I _D = 10 A		0.12	0.16	Ω
Input Capacitance	Ciss	V _{DS} = 10 V		1720		pF
Output Capacitance	Coss	V _{GS} = 0 V		330		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		170		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 125 V, I _D = 10 A		17		ns
Rise Time	tr	V _{GS} = 10 V		17		ns
Turn-off Delay Time	td(off)	R _G = 0 Ω		49		ns
Fall Time	tf			9		ns
Total Gate Charge	QG	V _{DD} = 200 V		47		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		7		nC
Gate to Drain Charge	Q _{GD}	I _D = 20 A		25		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 20 A, V _{GS} = 0 V		0.91		V
Reverse Recovery Time	trr	I _F = 20 A, V _{GS} = 0 V		210		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		1.4		μC

Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY



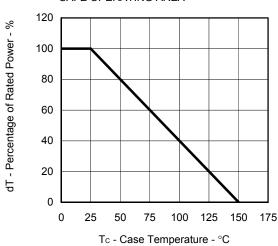
TEST CIRCUIT 2 SWITCHING TIME



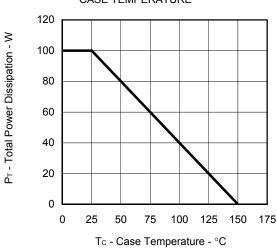
TEST CIRCUIT 3 GATE CHARGE

TYPICAL CHARACTERISTICS (TA = 25°C)

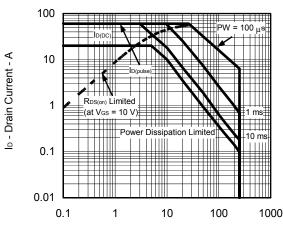
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



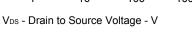
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



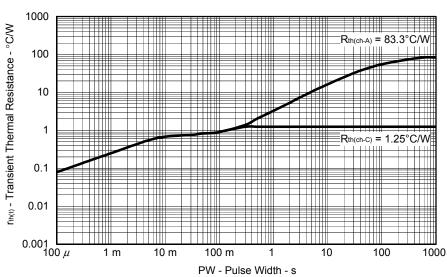
FORWARD BIAS SAFE OPERATING AREA



10 ms

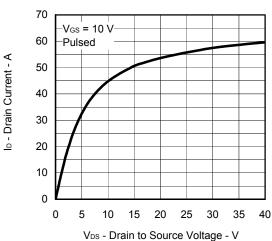


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

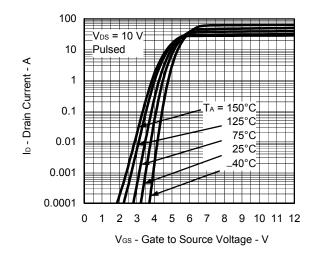


3

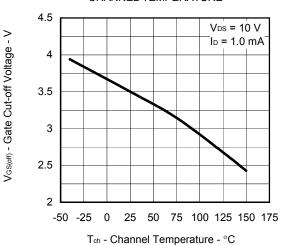
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



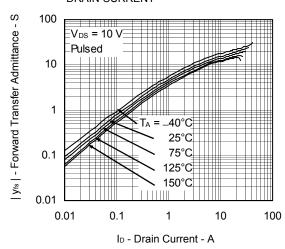
FORWARD TRANSFER CHARACTERISTICS



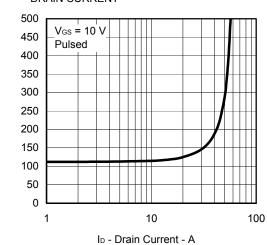
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



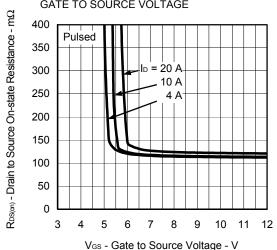
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



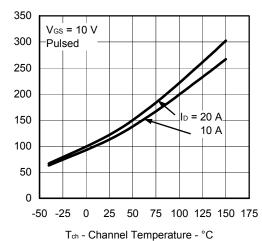
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



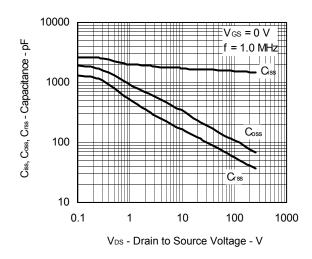
RDS(m) - Drain to Source On-state Resistance - m\Omega

RDS(on) - Drain to Source On-state Resistance - m\Omega

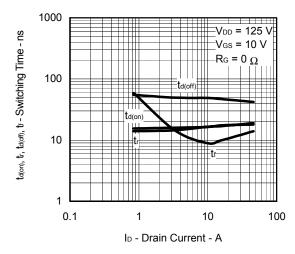
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



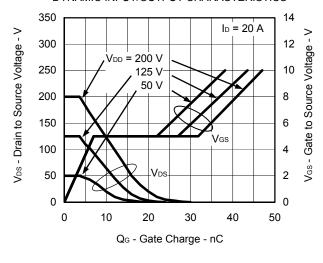
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



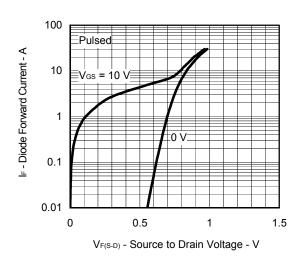
SWITCHING CHARACTERISTICS



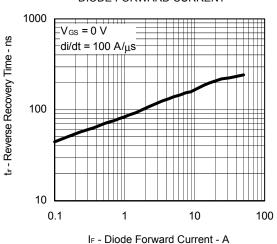
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

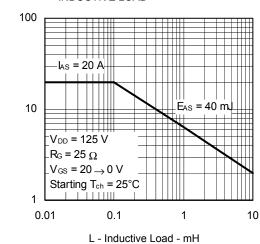


REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

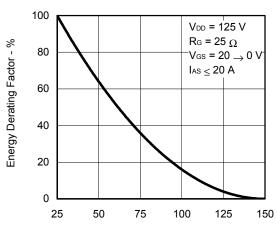


IAS - Single Avalanche Current - A

SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



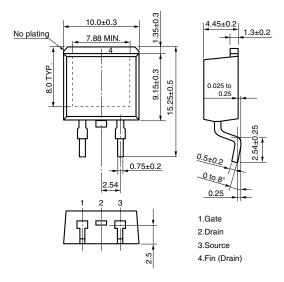
SINGLE AVALANCHE ENERGY DERATING FACTOR



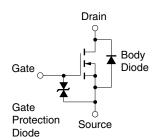
Starting Tch - Starting Channel Temperature - °C

PACKAGE DRAWING (Unit: mm)

TO-263 (MP-25ZK)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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